

EAST Search History

EAST Search History (Prior Art)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S54	3	"20050174845"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/06/04 18:10
S55	2	WO near2 "9607300"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/06/04 18:10
S56	1	1996-160638.NRAN.	DERWENT	ADJ	ON	2010/06/04 18:10
S57	18	"5195010"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/06/04 18:10
S58	5633	heat\$3 with silicon with (voltage or current)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/06/04 18:10
S59	317	(chang\$3 or alter\$3 or convert\$3) with silicon with (current or voltage) with heat\$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/06/04 18:10
S60	2	(chang\$3 or alter\$3 or convert\$3) with silicon with (current or voltage) with heat\$3 with (source and drain)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/06/04 18:10
S61	15	(chang\$3 or alter\$3 or convert\$3) with ((poly silicon) or (polycrystalline silicon) or (poly\$1Si)) with (current or voltage) with heat\$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/06/04 18:10

S62	10	(chang\$3 or alter\$3 or convert\$3) with (SiGe or (silicon germanium)) with (current or voltage) with heat\$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/06/04 18:10
S63	662	(MURAKAMI near2 SHIGERU).inv.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/06/04 18:10
S64	29	(YAMAGATA near2 YASUJI).inv.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/06/04 18:10
S65	4485	(257/16,49,52,59).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/06/04 18:10
S66	724	(257/64,68).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/06/04 18:10
S67	1281	(257/770-772).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/06/04 18:10
S68	390	(438/153).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/06/04 18:10
S69	1654	(438/166).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/06/04 18:10
S70	3009	(438/238-239).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/06/04 18:10
S71	1476	(438/478).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2010/06/04 18:10
S72	3	"20020126108"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/06/04 18:10
S73	13807	((write near2 once) memory) or (WOM)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/06/04 18:10
S74	12417	(semiconductor (film or material)) same ((amorphous silicon) or (a \$1silicon) or (a\$1Si))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/06/04 18:10

S75	63	S73 and S74	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/06/04 18:10
S76	10427	((write near2 once) memory) or (one time programmable) or (OTP)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/06/04 18:10
S77	24817	(semiconductor (film or material)) same ((amorphous silicon) or (a \$1silicon) or (a\$1Si) or (SiGe) or (Silicon Germanium))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/06/04 18:10
S78	238	S76 and S77	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/06/04 18:10
S79	291	((gate or dielectric or insulat \$3) and (semiconductor)) and (((write near2 once) memory) or (one time programmable) or (OTP)). ti.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/06/04 18:11
S80	8	((thin film transistor) or (thinfilm transistor) or TFT) and S79	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/06/04 18:11
S81	1	jp "56044198"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/06/04 18:11
S82	185	"20030198077" "20050098811" "20050194645" "20060054894" "20060175648" "5850090" "5994730" "6384439" "6465828" "6555420" "6576948" "6583490" "6690031" "6958740" "7113420" "7368343"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/04 18:11

S83	53854	voltage same increas\$3 same resistance same (semiconductor (film or material or layer))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/04 18:11
S84	51204	((write near2 once) memory) or (one time programmable) or (OTP)) and S83	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2010/06/04 18:11
S85	2657	((thin film transistor) or (thinfilm transistor) or TFT) and S84	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/06/04 18:11
S86	136	memory.ti. and S85	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/06/04 18:11
S87	1278	((apply\$3 or programm\$4 or operat\$3) near3 voltage) same (alter\$3 or chang\$3 or convert\$3) same (semiconductor (film or material or layer))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/06/04 18:11
S88	229	((thin film transistor) or (thinfilm transistor) or TFT) and S87	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/06/04 18:11
S89	10	((write near2 once) memory) or (one time programmable) or (OTP)) and S88	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/06/04 18:11
S90	2702	voltage same increas\$3 same resistance same (semiconductor (film or material or layer))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/06/04 18:11
S91	20	((write near2 once) memory) or (one time programmable) or (OTP)) and S90	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/06/04 18:11

S93	43363	((write near once) or (WOM)) or (one time programmable) or (OTP)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/11/03 16:02
S94	2732	(semiconductor (film or material)) near ((amorphous silicon) or (a \$1silicon) or (a\$1Si))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/11/03 16:03
S95	18	S93 and S94	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/11/03 16:03
S96	43363	((write near once) or (WOM)) or (one time programmable) or (OTP)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/11/03 17:26
S97	1223	(semiconductor (film or material)) and S96	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/11/03 17:26
S98	780	gate and S97	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/11/03 17:27
S99	743	voltage and S98	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/11/03 17:27
S100	658	(insulat\$3 or dielectric or (gate oxide)) and S99	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/11/03 17:28
S102	190	((((non\$1conduct\$3) or conduct\$3 or insulat\$3 or (open circuit)) near (state or phase)) and S100	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/11/03 17:34

S103	19	((thinfilm or (thin film)) transistor) same (semiconductor (layer or material)) same ((conduct \$3 or (non\$1conduct\$3 or insulat\$3)) (state or phase))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/11/03 19:08
S104	1	WO "2008041716"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/11/03 19:29
S105	5	"7714408"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/11/03 19:41
S107	1	JP "56044198"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/11/03 19:46
S108	24	"5798534"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/11/03 19:51
S114	3	"20020126108"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/11/04 10:03
S115	976	memory near ((thinfilm or (thin film)) (transistor) or TFT)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/11/04 10:11
S116	906	(gate or source or drain) and S115	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/11/04 10:12

S117	813	(insulat\$3 or (gate oxide) or dielectric) and S116	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/11/04 10:12
S118	149	(fuse) and S117	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/11/04 10:16
S119	43	"5854494"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/11/04 10:59
S120	27	("5406509").PN. OR ("5457649").URPN.	US-PGPUB; USPAT; USOCR	ADJ	ON	2010/11/04 11:40
S121	28	"5457649"	US-PGPUB; USPAT; USOCR	ADJ	ON	2010/11/04 11:43
S122	1	"5457649"	DERWENT	ADJ	ON	2010/11/04 11:44
S123	12	((thinfilm or (thin film)) (transistor) or TFT) with (gate spacer)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/11/04 12:18
S124	1	10/573527	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2010/11/04 12:23
S125	1	"5953596"	DERWENT	ADJ	ON	2010/11/04 12:24

EAST Search History (I nterference)

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